

N-Channel Enhancement Mode Field Effect Transistor

General Description

The CMSA150N03L uses advanced technology to provide excellent RDS (ON) . This device is suitable to be used as the low side FET in SMPS,load switching and general purpose.

Features

- Lower On-resistance
- Simple Drive Requirement
- 100% EAS Guaranteed
- RoHS Compliant

Absolute Maximum Ratings

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	30	V
V_{GS}	Gate-Source Voltage	± 20	V
$I_D@T_C=25^{\circ}C$	Continuous Drain Current	120	A
$I_D@T_C=100^{\circ}C$	Continuous Drain Current	96	A
I_{DM}	Pulsed Drain Current	360	A
EAS	Single Pulse Avalanche Energy ¹	260	mJ
$P_D@T_C=25^{\circ}C$	Total Power Dissipation	50	W
T_{STG}	Storage Temperature Range	-55 to 150	$^{\circ}C$
T_J	Operating Junction Temperature Range	-55 to 150	$^{\circ}C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JA}$	Junction-to-Ambient	---	50	$^{\circ}C/W$
$R_{\theta JC}$	Junction-to-Case	---	1.6	$^{\circ}C/W$

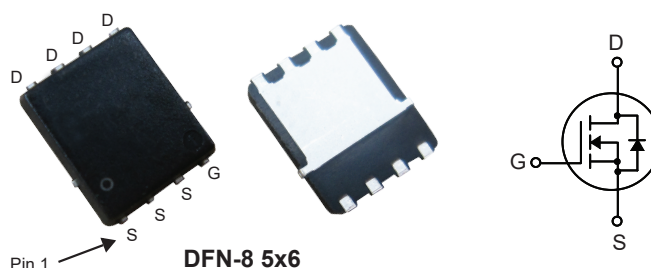
Product Summary

BVDSS	RDSON	ID
30V	3.3m Ω	120A

Applications

- Load Switch
- Power Management in Notebook Computer, Portable Equipment and Battery Powered Systems.

DFN-8 5x6 Pin Configuration



Type	Package	Marking
CMSA150N03L	DFN-8 5x6	CMSA150N03L

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Electrical Characteristics ($T_J=25^{\circ}\text{C}$, unless otherwise noted)

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{GS}=0V$, $I_D=250\mu A$	30	---	---	V
$R_{DS(ON)}$	Static Drain-Source On-Resistance	$V_{GS}=10V$, $I_D=20A$	---	---	3.3	m Ω
		$V_{GS}=4.5V$, $I_D=15A$	---	---	7.5	
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS}=V_{DS}$, $I_D=250\mu A$	1	---	3	V
I_{DSS}	Drain-Source Leakage Current	$V_{DS}=30V$, $V_{GS}=0V$, $T_J=25^{\circ}\text{C}$	---	---	1	μA
I_{GSS}	Gate-Source Leakage Current	$V_{GS}=\pm 20V$, $V_{DS}=0V$	---	---	± 100	nA
g_{fs}	Forward Transconductance	$V_{DS}=5V$, $I_D=15A$	---	23	---	S
R_g	Gate Resistance	$V_{DS}=0V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2.5	---	Ω
Q_g	Total Gate Charge	$V_{DD}=15V$, $I_D=23A$ $V_{GS}=10V$	---	40	---	nC
Q_{gs}	Gate-Source Charge		---	8	---	
Q_{gd}	Gate-Drain Charge		---	5	---	
$T_{d(on)}$	Turn-On Delay Time	$V_{DD}=15V$, $R_G=6\Omega$ $I_D=23A$, $V_{GEN}=10V$	---	15	---	ns
T_r	Rise Time		---	6	---	
$T_{d(off)}$	Turn-Off Delay Time		---	33	---	
T_f	Fall Time		---	5	---	
C_{iss}	Input Capacitance	$V_{DS}=15V$, $V_{GS}=0V$, $f=1\text{MHz}$	---	2800	---	pF
C_{oss}	Output Capacitance		---	300	---	
C_{rss}	Reverse Transfer Capacitance		---	270	---	

Diode Characteristics

Symbol	Parameter	Conditions	Min.	Typ.	Max.	Unit
I_S	Continuous Source Current	$V_G=V_D=0V$, Force Current	---	---	120	A
I_{SM}	Pulsed Source Current		---	---	360	A
V_{SD}	Diode Forward Voltage	$V_{GS}=0V$, $I_F=15A$	---	---	1.2	V

Note :

1.The EAS data shows Max. rating . The test condition is $V_{DD}=25V$, $V_{GS}=10V$, $L=0.5\text{mH}$, $I_{AS}=32.5A$.

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Typical Characteristics

